2SD1366

Silicon NPN Epitaxial

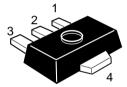
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Application

Low frequency power amplifier

Outline

UPAK



- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector (Flange)



2SD1366

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V _{CEO}	20	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	1	A
Collector peak current	i _{C(peak)} *1	1.5	A
Collector power dissipation	P _c * ²	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 ms, Duty cycle \leq 20%.

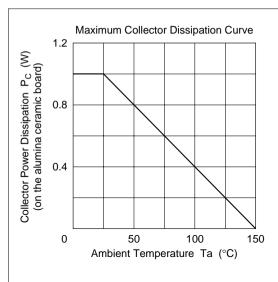
2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

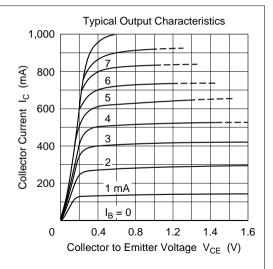
Electrical Characteristics ($Ta = 25^{\circ}C$)

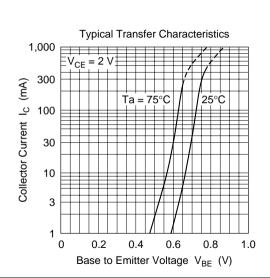
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{\text{(BR)CEO}}$	20	_	_	V	I_{C} = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_		0.1	μΑ	$V_{EB} = 4 \text{ V}, I_C = 0$
DC current transfer ratio	h _{FE} *1	85	_	240		$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}, \text{ Pulse}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.15	0.3	V	$I_{\rm C}$ = 0.8 A, $I_{\rm B}$ = 0.08 A, Pulse
Base to emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	_	0.9	1.0	V	$I_{\rm C}$ = 0.8 A, $I_{\rm B}$ = 0.08 A, Pulse
Gain bandwidth product	f _T	_	240	_	MHz	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}, \text{ Pulse}$
Collector output capacitance	Cob	_	22	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

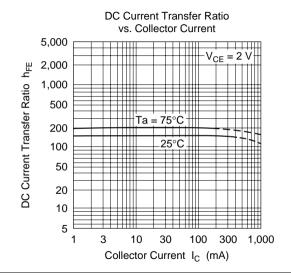
Note: 1. The 2SD1366 is grouped by h_{FE} as follows.

Mark AA		AB	
h _{FE}	85 to 170	120 to 240	

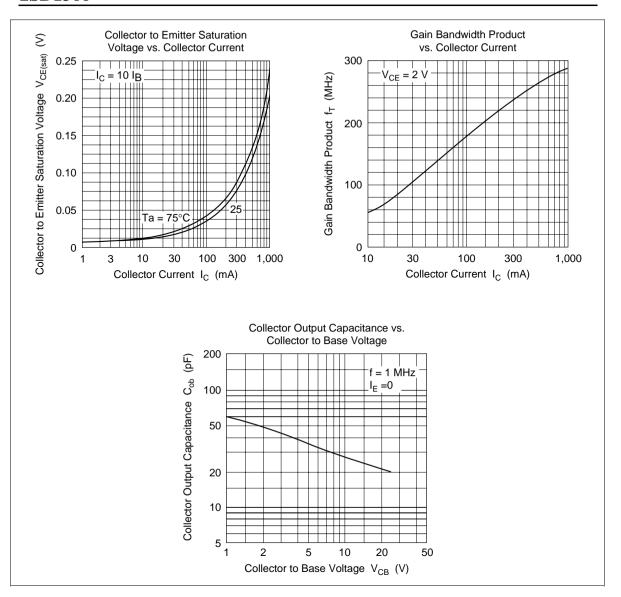




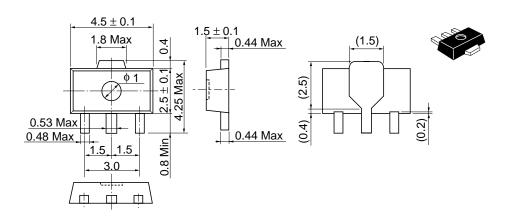




2SD1366



Unit: mm



Hitachi Code	UPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.050 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0

Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.

Electronic Components Group.

Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000

Tel: <44> (1628) 585000 Fax: <44> (1628) 778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666

Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218

Fax: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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